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IN THE CLAIMS

1	Claim 1 (currently amended): A method for fabricating a silicon based package (SBP) in
2	the sequence as follows:
. 3	starting with a wafer composed of silicon and having a first surface and a reverse
4	surface which are planar as the base for the SBP,
5	then forming an interconnection structure including multilayer conductor patterns
6	over the first surface; [[,]]
7	then forming a protective overcoat layer over the interconnnection structure; [[, and]]
8	then forming a temporary bond between the protective overcoat layer of the SBP and
9	a wafer holder, with the wafer holder being a rigid structure; [[,]]
10	then thinning the reverse surface of the wafer to a desired thickness to form an ultra
11	thin silicon wafer (UTSW) for the SBP; [[,]]
12	then forming via holes which extend through the UTSW; [[,]]
13	then forming metallization in the via holes with the metallization extending through
14	the UTSW; and
15	then remove removing the temporary bond.
1	Claim 2 (previously presented): The method of claim 1 including bonding the metallization
2	in the via holes to pads of a carrier.
1	Claim 3 (previously presented): The method of claim 1 including forming capture pads on
2	the first surface prior to thinning the wafer.
1	Claim 4 (currently amended): The method of claim 1 including:
2	initially forming capture pads on the first surface; [[,]]
3	then forming the interconnection structure over the first surface and the capture
4	pads <u>:</u> [[,]]
5	then forming the temporary bond of the wafer holder to the reverse surface; [[,]] and
6	then thinning the wafer, thereby forming the UTSW.

Claim 5 (currently amended): The method of claim 1 including:				
initially forming capture pads on the first surface; [[,]]				
then forming interconnection structure over the first surface and the capture pads;				
[[,]]				
then forming the temporary bond of the wafer holder to the reverse surface,				
then thinning the wafer, thereby forming the UTSW; [[,]] and				
then forming the via holes through the UTSW down to the capture pads.				
Claim 6 (currently amended): The method of claim 1 including:				
initially forming capture pads on the first surface; [[,]]				
then forming interconnection structure over the first surface and the capture pads,				
then forming the temporary bond of the wafer holder to the reverse surface,				
then thinning the wafer, thereby forming the UTSW; [[,]]				
then forming the via holes through the UTSW down to the capture pads; [[,]]				
then forming a dielectric layer over the surface of the wafer leaving the bottoms of the				
via holes clear with the capture pads exposed; [[,]] and				
then forming the metallization in the via holes in contact with the capture pads.				
Claim 7 (currently amended): The method of claim 1 including:				
initially forming capture pads on the first surface; [[,]]				
then forming interconnection structure over the first surface and the capture pads				
then forming the temporary bond of the wafer holder to the reverse surface; [[,]]				
then thinning the wafer, thereby forming the UTSW; [[,]]				
then forming the via holes through the UTSW down to the capture pads; [[,]]				
then forming a dielectric layer over the surface of the wafer leaving the bottoms of the				
via holes clear with the capture pads exposed; [[,]]				

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and

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then [[form]] forming metal joining structures on the metal pads.

then depositing metal pads into the via holes in contact with the capture pads; [[,]]

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Claim 8 (previously presented): The method of claim 1 including initially forming via holes 1 2 in the first surface prior to thinning the wafer. Claim 9 (currently amended): The method of claim 1 including the steps as follows: 1 initially forming via holes in the first surface prior to thinning the wafer ; [[,]] 2 then forming a dielectric layer covering the via holes. 3 Claim 10 (currently amended): The method of claim 1 including the steps as follows: 1 2 initially forming via holes in the first surface prior to thinning the wafer; [[,]] then forming a dielectric layer over the surface of the wafer including the via holes; 3 [[,]] and 4 then forming a through via/cap pad layer of a first metal layer over dielectric layer 5 including the via holes. 6 Claim 11 (currently amended): The method of claim 1 including the steps as follows: 1 initially forming via holes in the first surface prior to thinning the wafer; [[,]] 2 then forming a dielectric layer over the surface of the wafer including the via holes, 3 then forming a through via/cap pad layer of a first metal layer over dielectric layer 4 including the via holes; [[,]] and 5 then planarizing to remove the via/cap pad layer above the surface of the dielectric 6 layer, thereby forming vias in the via holes. 7

Claim 12 (currently amended): The method of claim 1 including the steps as follows:	
initially forming via holes in the first surface prior to thinning the wafer; [[,]]	
then forming a dielectric layer over the surface of the wafer including the via holes	
then forming a through via/cap pad layer of a first metal layer over dielectric lay	
including the via holes; [[,]]	
then planarizing to remove the via/cap pad layer above the surface of the dielectric	
layer, thereby forming vias in the via holes; [[,]] and	
then forming an interconnection structure over the first surface including the first	
metal layer.	
Claim 13 (currently amended): The method of claim 1 including the steps as follows:	
initially forming via holes in the first surface prior to thinning the wafer; [[,]]	
then forming a dielectric layer over the surface of the wafer including the via hole	
then forming a through via/cap pad layer of a first metal layer over dielectric layer	
including the via holes; [[,]]	
then planarizing to remove the via/cap pad layer above the surface of the dielectric	
layer, thereby forming vias in the via holes ; [[,[and]]	
then forming interconnection structure over the first surface including the metal v	
and the first metal layer; [[,]]	
then forming the temporary bond to the rigid wafer holder on the reverse surface;	
[[,]] and	
then thinning the wafer to the desired thickness of the UTSW.	

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Please cancel claims 14-16 without prejudice to pursuit of the subject matter thereof in a divisional application.

Claims 14 - 24 (canceled)

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1	Claim 25 (currently amended): A method for fabricating a	Silicon Based Pac	kage (SBP) in		
2	the sequence as follows:				
3	starting with a wafer composed of silicon and having a first surface and a reverse				
4	surface which are planar as the base for the SBP; [[,]]				
5	then forming an interconnection structure including multilayer conductor patterns				
6	over the first surface; [[,]]				
7	7 then forming a protective overcoat layer composed of polyimide over the				
8	interconnnection structure; [[,]]				
9	then forming a temporary bond between the protective overcoat layer of the SBP and				
10	a wafer holder, with the wafer holder being a rigid structure; [[,]]				
11	then thinning the reverse surface of the wafer to a desired thickness to form an Ultra				
12	Thin Silicon Wafer (UTSW) for the SBP; [[,]]				
13	then forming via holes which extend through the UTSW; [[,]]				
14	then forming metallization in the via holes with the metallization extending through				
15	the UTSW; [[,]] and				
16	then removing the temporary bond.				
	•				
1	Claim 26 (currently amended): The method of claim 25 incl	uding:			
2	forming the temporary bond with polyimide; [[,]], and				
3	releasing the temporary bond by laser ablation.				

Please cancel claim 27 without prejudice to pursuit of the subject matter thereof in a divisional application.

Claims 27 (canceled)

Claim 30 (currently amended): The method of claim 1 [[29]] including the UTSW having a
desired thickness including the steps performed in the sequence as follows:
performing a step of forming an interconnection structure including multilayer
conductor patterns over the first surface of the silicon wafer;
then forming a protective overcoat layer over the interconnnection structure,
[[then]] the step of forming the temporary bond between the protective overcoat layer
of the SBP and the wafer holder leaving the reverse surface exposed;
then thinning the reverse surface of the wafer to a desired thickness to form the
UTSW for the SBP;
then forming the via holes which extend extending through the thickness of the
UTSW; and

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Please cancel claim 31 without prejudice to pursuit of the subject matter thereof in a divisional application.

then forming the metallization in the via holes with the metallization extending

Claim 31 (canceled)

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through the thickness of the UTSW. [[; and]]

thereafter releasing the temporary bond.

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